IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

JAN 2 3 2004 H In the Application of REN, et al.

Serial No.: 10/649,712

Examiner:

Date Filed:

August 26, 2003

Group: 2812

For: GAN-TYPE ENHANCEMENT MOSFET USING HETERO STRUCTURE

CERTIFICATE UNDER 37 CFR 1.8(a)

I hereby certify that this correspondence is being deposited with the U.S. Postal Service as First Class mail in an envelope addressed to the Commissioner for

Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

Neil R. Jetter Esq.

TRANSMITTAL LETTER

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Please find enclosed for filing the following:

X Supplemental Information Disclosure Statement, with PTO/SB/08A and PTO/SB/08B, and references; and

X 1 postcard.

Although no fee is believed due, please charge any underpayment to Deposit Account No.

50-0951. This letter is submitted in duplicate.

Respectfully submitted,

AKERMAN SENTER

Dated: 1/20/04

Neil R. Jetter Esq.

Registration No. 46,803 222 Lakeview Avenue, Suite 400

West Palm Beach, FL 33402-3188

Tel: 561-653-5000

Docket No. 5853-274